

TOSHIBA

2SK880

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL JUNCTION TYPE

2SK880

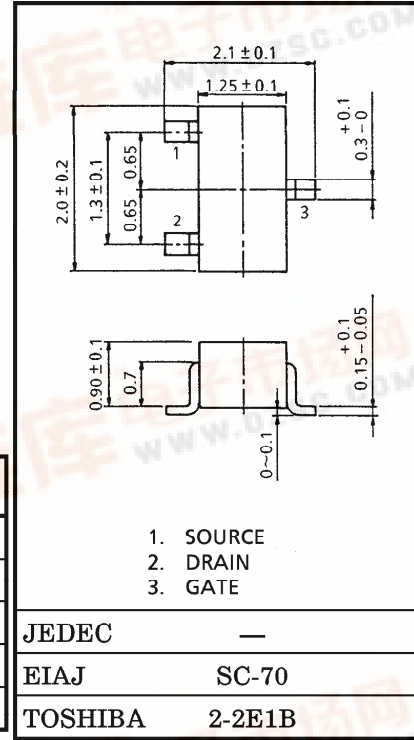
AUDIO FREQUENCY LOW NOISE AMPLIFIER APPLICATIONS

Unit in mm

- High $|Y_{fs}|$: $|Y_{fs}| = 15\text{mS (Typ.) at } V_{DS} = 10\text{V, } V_{GS} = 0$
- High Breakdown Voltage : $V_{GDS} = -50\text{V}$
- Low Noise : $NF = 1.0\text{dB (Typ.) at } V_{DS} = 10\text{V, } I_D = 0.5\text{mA, } f = 1\text{kHz, } R_G = 1\text{k}\Omega$
- High Input Impedance : $I_{GSS} = -1\text{nA (Max.) at } V_{GS} = -30\text{V}$
- Small Package

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	V_{GDS}	-50	V
Gate Current	I_G	10	mA
Drain Power Dissipation	P_D	100	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~125	$^\circ\text{C}$

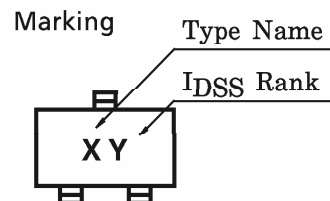


ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Weight : 0.006g

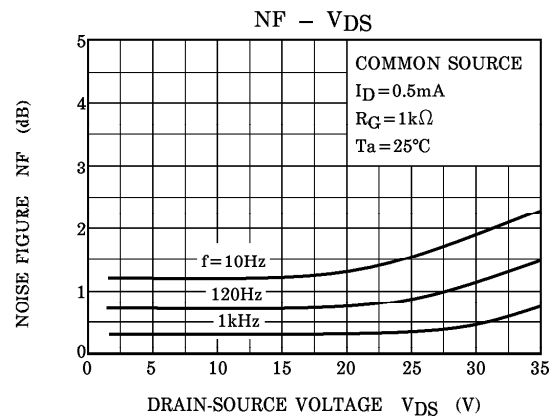
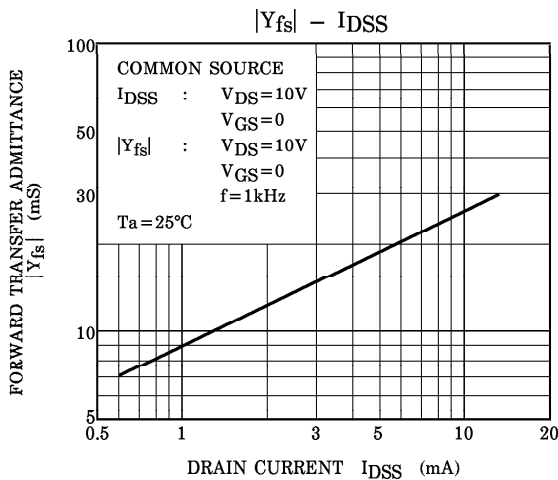
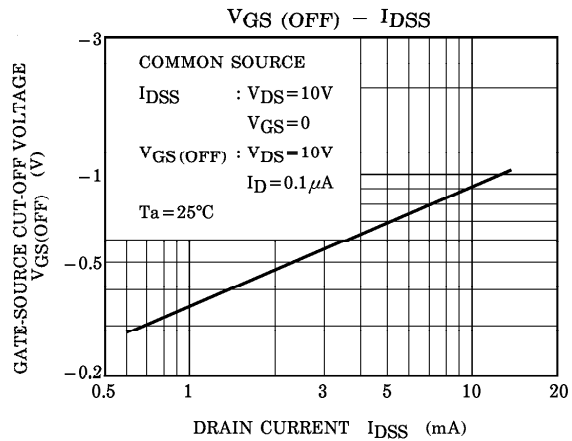
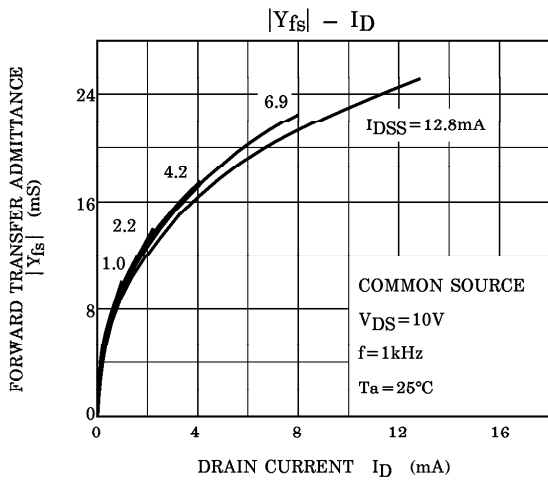
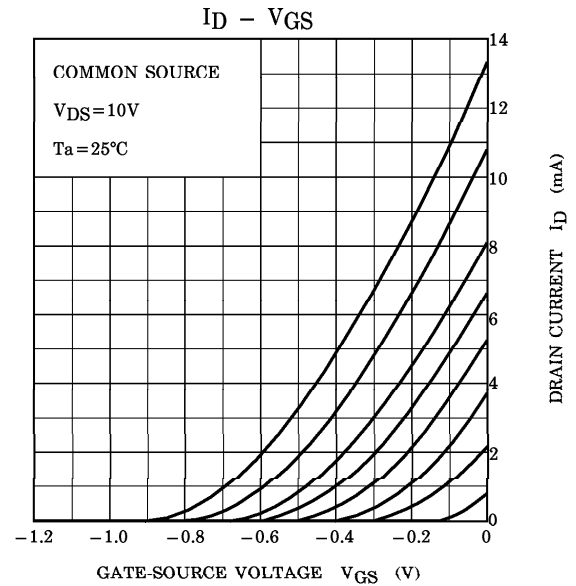
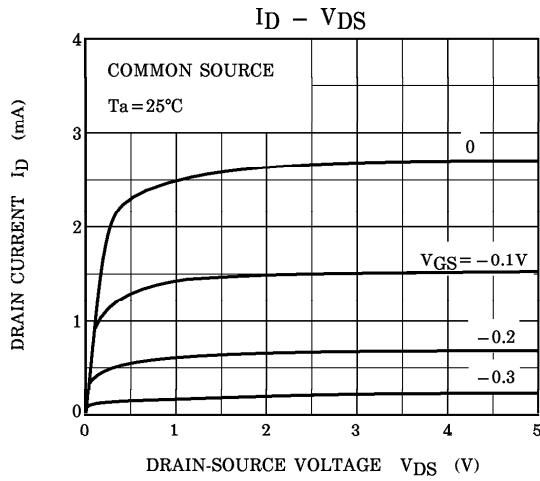
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Cut-off Current	I_{GSS}	$V_{GS} = -30\text{V, } V_{DS} = 0$	—	—	-1.0	nA
Gate-Drain Breakdown Voltage	$V_{(BR)GDS}$	$V_{DS} = 0, I_G = -100\mu\text{A}$	-50	—	—	V
Drain Current	$I_{DSS} \text{ (Note)}$	$V_{DS} = 10\text{V, } V_{GS} = 0$	1.2	—	14.0	mA
Gate-Source Cut-off Voltage	$V_{GS} \text{ (OFF)}$	$V_{DS} = 10\text{V, } I_D = 0.1\mu\text{A}$	-0.2	—	-1.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V, } V_{GS} = 0, f = 1\text{kHz}$	4.0	15	—	mS
Input Capacitance	C_{iss}	$V_{DS} = 10\text{V, } V_{GS} = 0, f = 1\text{MHz}$	—	13	—	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DG} = 10\text{V, } I_D = 0, f = 1\text{MHz}$	—	3	—	pF
Noise Figure	NF (1)	$V_{DS} = 10\text{V, } R_G = 1\text{k}\Omega, I_D = 0.5\text{mA, } f = 10\text{Hz}$	—	5	—	dB
	NF (2)	$V_{DS} = 10\text{V, } R_G = 1\text{k}\Omega, I_D = 0.5\text{mA, } f = 1\text{kHz}$	—	1	—	dB

Note : I_{DSS} Classification Y : 1.2~3.0mA, GR : 2.6~6.5mA, BL : 6.0~14mA

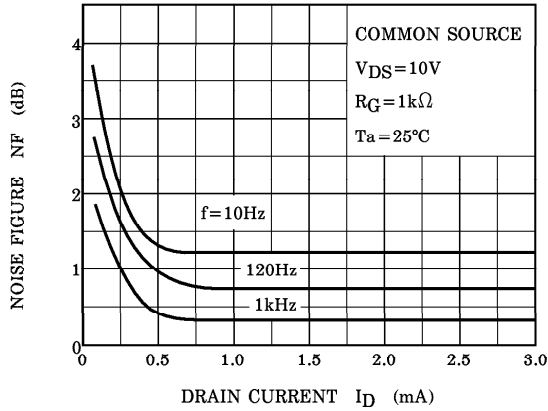


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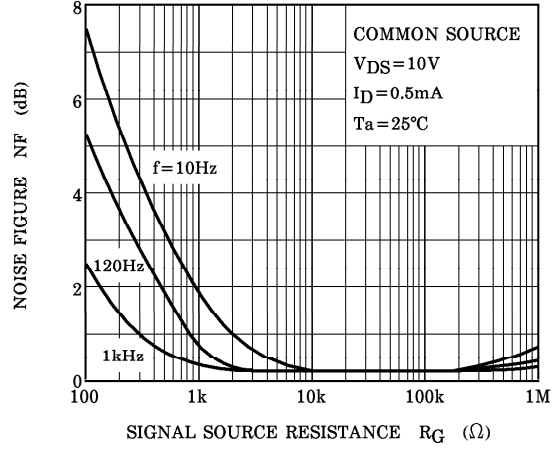
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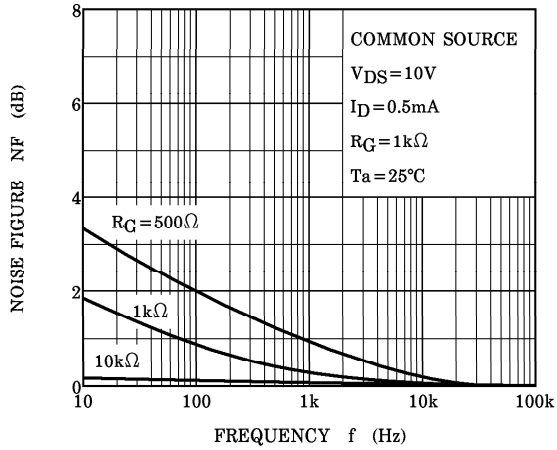
NF - I_D



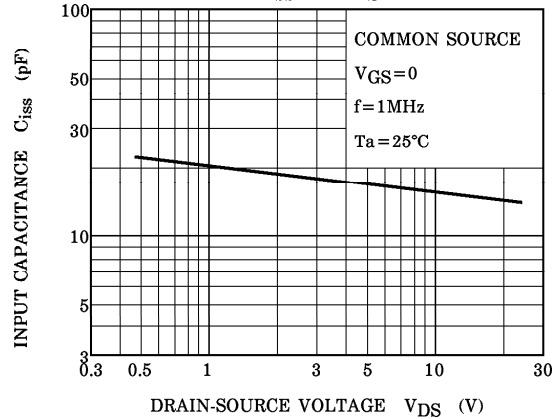
NF - R_G



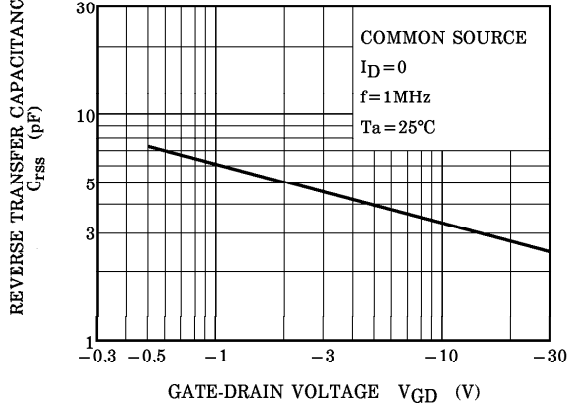
NF - f



C_{iss} - V_{DS}



C_{rss} - V_{GD}



P_D - T_a

